



ALPHA & OMEGA
SEMICONDUCTOR, LTD

AO4435

P-Channel Enhancement Mode Field Effect Transistor



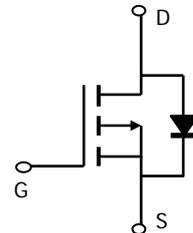
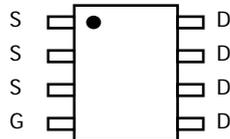
General Description

The AO4435 uses advanced trench technology to provide excellent $R_{DS(ON)}$, and ultra-low low gate charge with a 25V gate rating. This device is suitable for use as a load switch or in PWM applications. Standard Product AO4435 is Pb-free (meets ROHS & Sony 259 specifications).

Features

$V_{DS} = -30V$
 $I_D = -10A$ ($V_{GS} = -10V$)
 $R_{DS(ON)} < 18m\Omega$ ($V_{GS} = -10V$)
 $R_{DS(ON)} < 36m\Omega$ ($V_{GS} = -5V$)

SOIC-8
Top View



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	10 Sec	Steady State	Units	
Drain-Source Voltage	V_{DS}	-30		V	
Gate-Source Voltage	V_{GS}	± 25		V	
Continuous Drain Current ^A	I_D	$T_A=25^\circ C$	-10	-8	A
		$T_A=70^\circ C$	-8	-6	
Pulsed Drain Current ^B	I_{DM}	-80			
Power Dissipation ^A	P_D	$T_A=25^\circ C$	3.1	1.7	W
		$T_A=70^\circ C$	2.0	1.1	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150		$^\circ C$	

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	$t \leq 10s$	32	$^\circ C/W$
Maximum Junction-to-Ambient ^A		Steady State	60	$^\circ C/W$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	17	24	$^\circ C/W$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
B _V DSS	Drain-Source Breakdown Voltage	I _D = -250μA, V _{GS} = 0V	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -30V, V _{GS} = 0V T _J = 55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} = 0V, V _{GS} = ±25V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-1.7	-2.3	-3	V
I _{D(ON)}	On state drain current	V _{GS} = -10V, V _{DS} = -5V	-80			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} = -10V, I _D = -10A T _J = 125°C		15 22	18 27	mΩ
		V _{GS} = -5V, I _D = -5A		27	36	
g _{FS}	Forward Transconductance	V _{DS} = -5V, I _D = -10A		22		S
V _{SD}	Diode Forward Voltage	I _S = -1A, V _{GS} = 0V		-0.74	-1	V
I _S	Maximum Body-Diode Continuous Current				-3.5	A
DYNAMIC PARAMETERS						
C _{ISS}	Input Capacitance	V _{GS} = 0V, V _{DS} = -15V, f = 1MHz		1130	1400	pF
C _{OSS}	Output Capacitance			240		pF
C _{RSS}	Reverse Transfer Capacitance			155		pF
R _g	Gate resistance	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz		5.8	8	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} = -10V, V _{DS} = -15V, I _D = -10A		18	24	nC
Q _{g(4.5V)}	Total Gate Charge			9.5		
Q _{gs}	Gate Source Charge			5.5		nC
Q _{gd}	Gate Drain Charge			3.3		nC
t _{D(on)}	Turn-On Delay Time			8.7		ns
t _r	Turn-On Rise Time	V _{GS} = -10V, V _{DS} = -15V, R _L = 1.5Ω, R _{GEN} = 3Ω		8.5		ns
t _{D(off)}	Turn-Off Delay Time			18		ns
t _f	Turn-Off Fall Time			7		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F = -10A, dI/dt = 100A/μs		25	30	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F = -10A, dI/dt = 100A/μs		12		nC

A: The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using < 300 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C. The SOA curve provides a single pulse rating.

F: The current rating is based on the t ≤ 10s thermal resistance rating.

G: E_{AR} and I_{AR} ratings are based on low frequency and duty cycles to keep T_J = 25°C.

Rev0: Aug. 2007

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

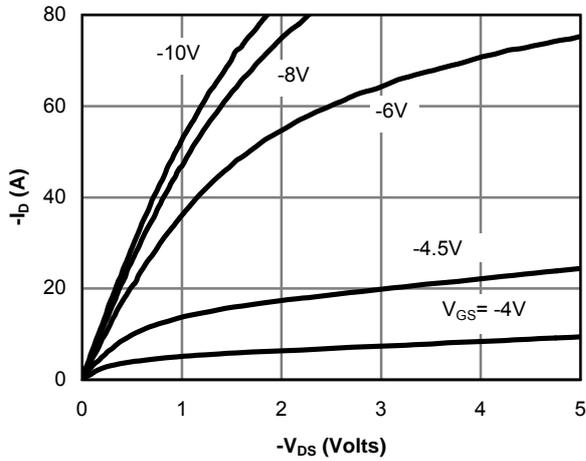


Figure 1: On-Region Characteristics

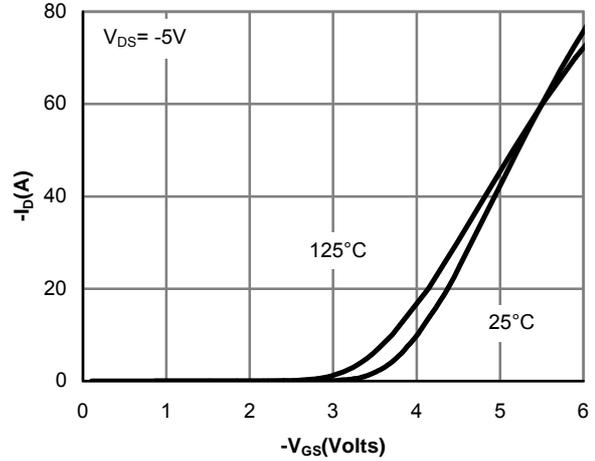


Figure 2: Transfer Characteristics

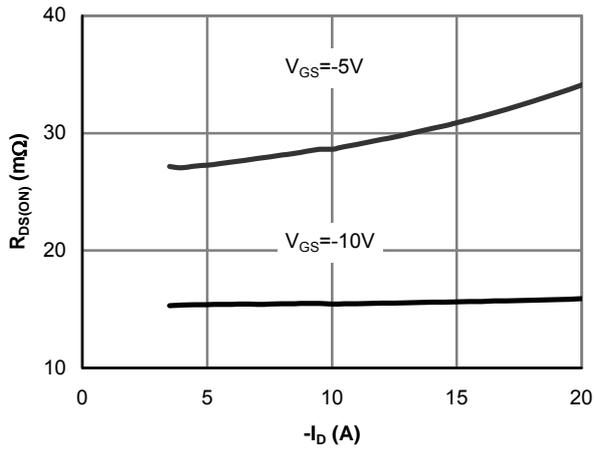


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

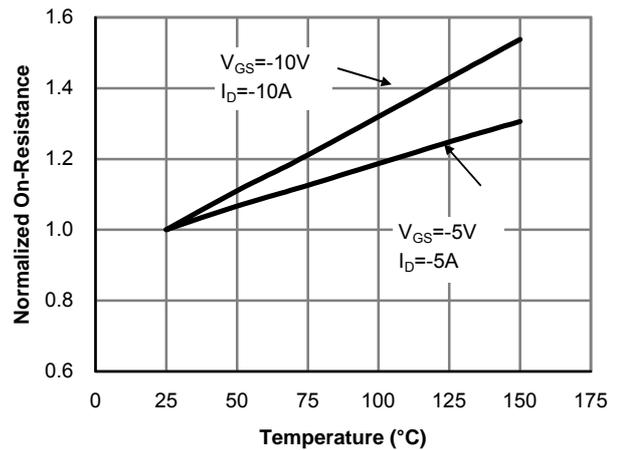


Figure 4: On-Resistance vs. Junction Temperature

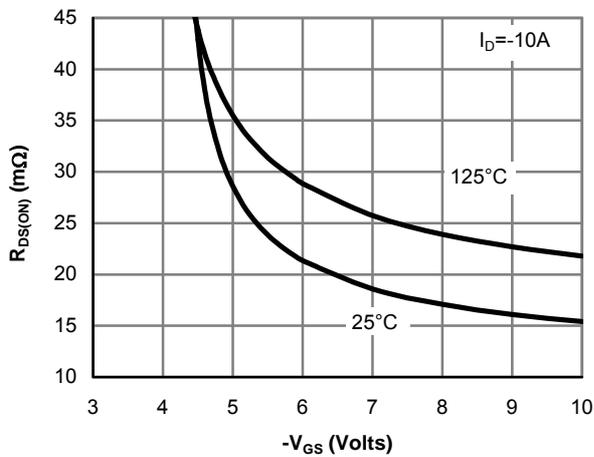


Figure 5: On-Resistance vs. Gate-Source Voltage

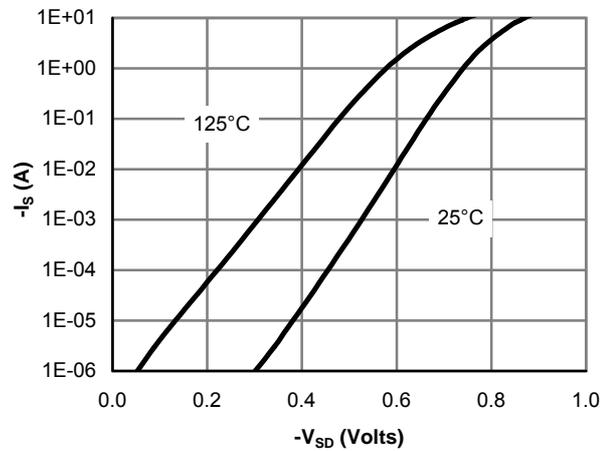


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

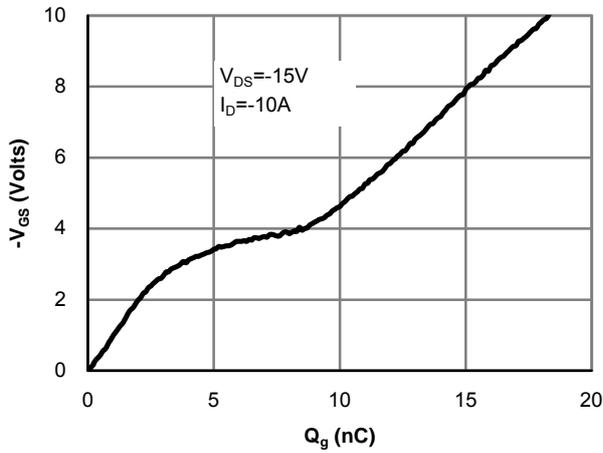


Figure 7: Gate-Charge Characteristics

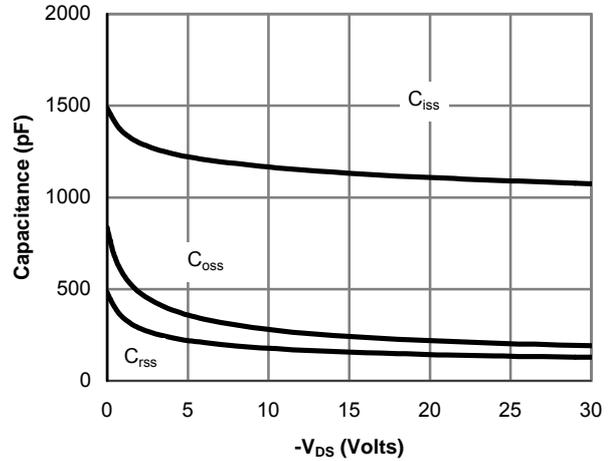


Figure 8: Capacitance Characteristics

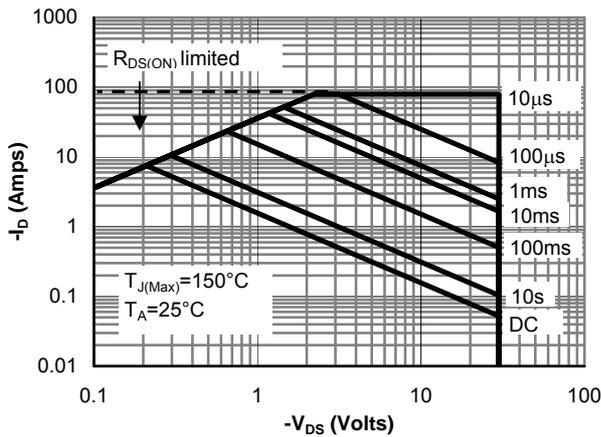


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

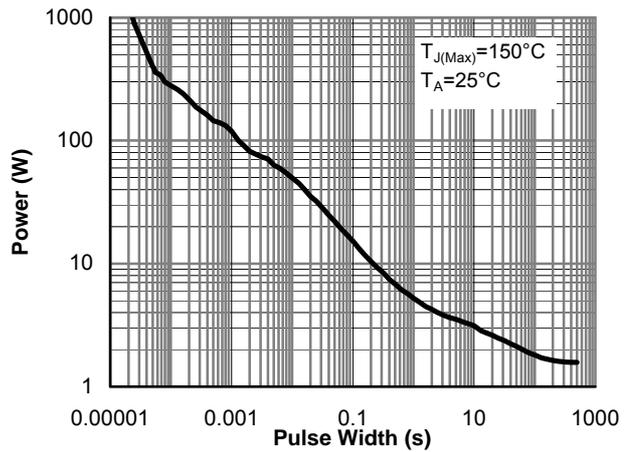


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

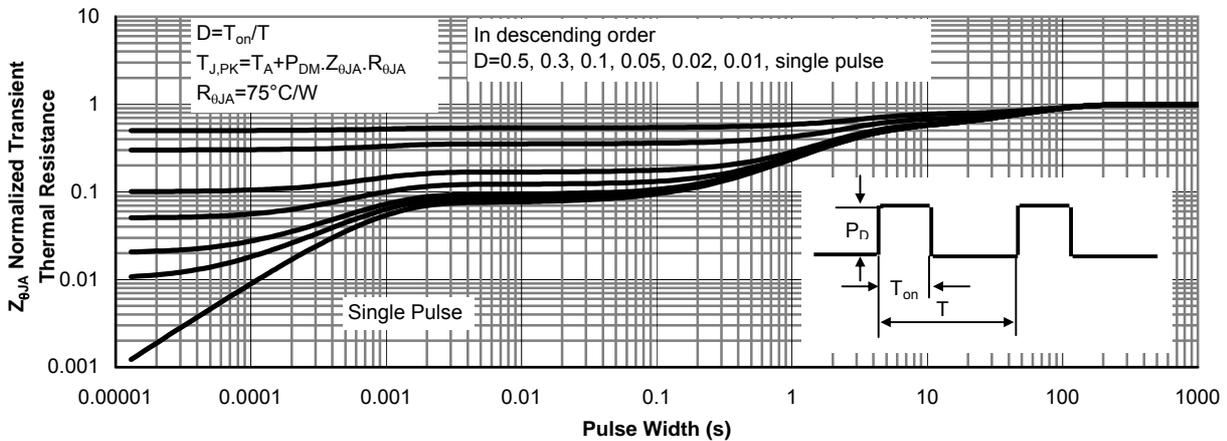


Figure 11: Normalized Maximum Transient Thermal Impedance (Note E)

This datasheet has been downloaded from:

www.EEworld.com.cn

Free Download

Daily Updated Database

100% Free Datasheet Search Site

100% Free IC Replacement Search Site

Convenient Electronic Dictionary

Fast Search System

www.EEworld.com.cn